

Amendments to the Specification:

Please replace the paragraph beginning at page 21, line 8, with the following amended paragraph:

Next, a second interlayer insulating film 117 made of a transparent organic film with a thickness of 1 to 3 $[\mu\text{m}]$ is formed on the first interlayer insulating film 116. In this embodiment mode, a second interlayer insulating film 117 is formed from an acrylic resin film with a thickness of 1.6 $[\mu\text{m}]$. Afterward, by the ordinary photolithography and dry etching, contact holes 118 are formed in the gate insulating film 110 present under the first interlayer film 116 as well as the second interlayer insulating film 117 and the first interlayer insulating film 116 (Fig.3C).

Please replace the paragraph beginning at page 26, line 8, with the following amended paragraph:

Figs. 5A and 5B show data as to I_D - V_G (current-voltage) characteristics of the n-channel type TFTs that were obtained through the measurements carried out with respect to eight n-channel type TFTs using a semiconductor measuring apparatus (4155B). Fig. 5A shows data obtained in the case where the step of forming a chemical oxide film made of an ultrathin silicon oxide film was employed and Fig. 5B shows data obtained in the case where the step of forming a chemical oxide film was omitted. Note that the channel length (L) and the channel width (W) of the n-channel type TFTs subjected to the measurement were 7.3 $[\mu\text{m}]$ and 200 $[\mu\text{m}]$, respectively.

Please replace the paragraph beginning at page 35, line 1, with the following amended paragraph:

Next, a second interlayer insulating film 356 made of an acrylic resin film with a thickness of 1.6 [[1μm]] μm is formed on the first interlayer insulating film 355. Afterward, contact holes are formed by the ordinary photolithography and dry etching so as to pass through the second interlayer insulating film 356, the first interlayer insulating film 355, and the gate insulating film 328 as an underlayer film. At this time, the contact holes are formed to be connected to the electrode 327 to function as a source wiring and the high-concentration impurity regions 342, 344, 345, 353, and 354 (see Fig. 10A).